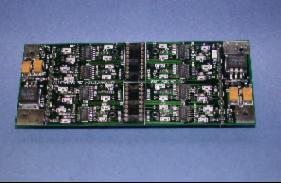
PHOTONIC32 CHANNEL DETECTOR PRE-AMP BOARD ASSEMBLY**DETECTORS INC.**Type PDB-707-100-XX

CAUTION: ESD SENSITIVE DEVICE

DESCRIPTION

PDB-707-100-XX This 32 channel Pre-Amplifier Board Assembly (PABA) is a side-by-side stackable platform with built-in voltage regulators, and eight precision CMOS quad op-amps. Low offset voltages and input bias currents, enhance operational stability at high voltage gains. Standard one meg feedback resistors produce a 1 KHz bandwidth, with optional selected resistors available. The following options can be used with this PABA.

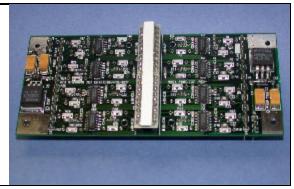


DESCRIPTION - OPTION D

PDB-707-100-D This option is designed to use two 16 element, blue enhanced silicon photodiode arrays. The arrays are on .062 [1.27] pitch with .010 [0.25] gaps. Each element is 2.51 mm² in size. The low leakage, high shunt detectors match up well with the CMOS op-amps on the PABA. This version can be used for optical color sorters, food processing, inspection equipment, optical scanners, and other multi-element photodiode array applications.

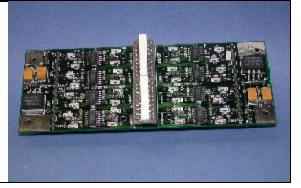
DESCRIPTION - OPTION DS

PDB-707-100-DS This option is designed to use two **PDB-C216S**, 16 element, blue enhanced silicon photodiode arrays, with X-ray fluoroscopic screens. The ZnCdS:Ag phosphorus doped screen emission spectrum is 530 nm (green). X-ray absorbtion is 9.66/26.7 KeV, with an effective atomic number of 38.4. This version is ideal for X-ray package inspection, diagnostic fluoroscopy and PCB examination.



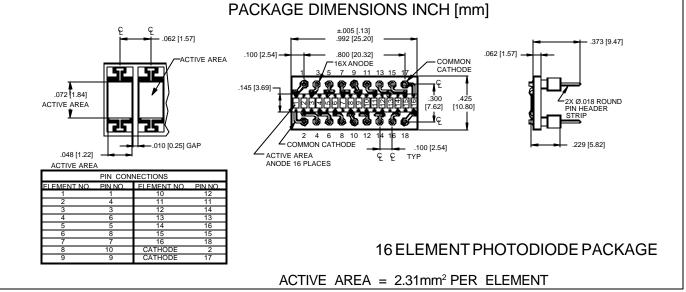
DESCRIPTION - OPTION DC

PDB-707-100-DC This option is designed to use two **PDB-C216C**, 16 element, blue enhanced silicon photodiode arrays, with cesium iodide thallium doped CsI (Ti), X-ray scintillation crystals. These arrays are used in 40 KeV to 120 Kev X-ray applications. Other uses include medical CT, baggage scanners, food processing and X-ray package inspection scanners.



Information in this technical data sheet is believed to be correct and reliable. However, no responsibility is assumed for possible inaccuracies or omission. Specifications are subject to change without notice. **PAGE 10F6** [FORMNO.100-PDB-707-100-XXREVE]

PHOTONIC 32 CHANNEL DETECTOR PRE-AMP BOARD ASSEMBLY DETECTORS INC. Type PDB-C216-SP Used on PDB-707-100-D



FEATURES

- DESCRIPTION
- .062 inch centers
- Stackable
- Blue enhanced
- Low capacitance

The **PDB-C216-SP** is a common cathode, monolithic silicon PIN photodiode 16 element array. Designed to be stacked end to end to form a line of optical pixels.

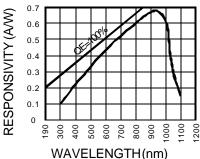
APPLICATIONS

- Cardreader
- Scanners
- Characterrecognition

ABSOLUTE MAXIMUM RATING (TA=25°C unless otherwise noted)

SYMBOL	PARAMETER	MIN	MAX	UNITS
V _{BR}	Reverse Voltage		50	V
T _{stg}	Storage Temperature	-40	+100	S
T _o	Operating Temperature Range	-20	+75	°C
T _s	Soldering Temperature*		+265	Ŷ
I	Light Current		500	mA

SPECTRALRESPONSE



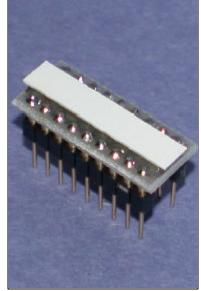
*1/16 inch from case for 3 secs max

ELECTRO-OPTICAL CHARACTERISTICS (TA=25°C unless otherwise noted, without scintillator)

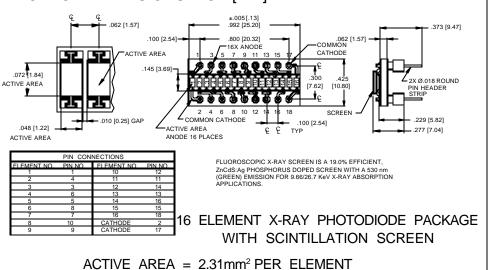
SYMBOL	CHARACTERISTIC	TEST CONDITIONS	MIN	TYP	MAX	UNITS
ع ع	Short Circuit Current	H = 100 fc, 2850 K	18	28		μA
Ι _D	Dark Current	$H = 0, V_{R} = 5 V$		5	50	nA
R _{SH}	Shunt Resistance	$H = 0, V_{R} = 10 \text{ mV}$	100	200		MΩ
TCR _{SH}	RSH Temp. Coefficient	$H = 0, V_{R} = 10 \text{ mV}$		-8		% / °C
CJ	Junction Capacitance	$H = 0, V_{R} = 0 V^{**}$		40	60	pF
λrange	Spectral Application Range	Spot Scan	350		1100	nm
λρ	Spectral Response - Peak	Spot Scan		950		nm
V _{BR}	Breakdown Voltage	I = 10 µLA	15	30		V
NEP	Noise Equivalent Power	V _R = 10 V @ Peak		2x10 ⁻¹⁴		W/√ ^{Hz}
tr	Response Time	$RL = 50 \Omega V_R = 10 V$		15		nS

Information in this technical data sheet is believed to be correct and reliable. However, no responsibility is assumed for possible inaccuracies or omission. Specifications [FORMNO.100-PDB-707-100-XXREVE] PAGE 2 OF 6 are subject to change without notice. ** f = 1 MHz

PHOTONIC32 CHANNEL DETECTOR PRE-AMP BOARD ASSEMBLY**DETECTORS INC.**Type PDB-C216-S Used on PDB-707-100-DS



PACKAGE DIMENSIONS INCH [mm]



FEATURES

- .062 inch centers
- Stackable
- Scintillation screen
- Low capacitance

The **PDB-C216-S** is a common cathode, monolithic silicon PIN photodiode 16 element array. Designed to be stacked end to end to form a line of pixels. Supplied with a fluoroscopic X-ray scintillation screen.

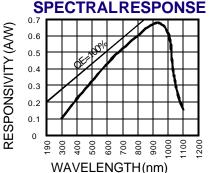
APPLICATIONS

- Luggage X-ray
- X-Ray scanner
- X-Ray inspection

ABSOLUTE MAXIMUM RATING (TA=25°C unless otherwise noted)

DESCRIPTION

SYMBOL	PARAMETER MIN MAX U		UNITS	
V _{BR}	Reverse Voltage		50	V
T _{STG}	Storage Temperature	-40	+100	°C
T _o	Operating Temperature Range	-20	+75	°C
Τ _s	Soldering Temperature*		+265	°C
Ι _L	Light Current		500	mA



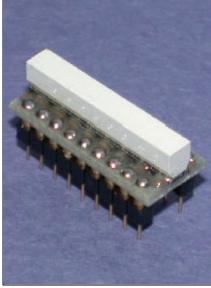
*1/16 inch from case for 3 secs max

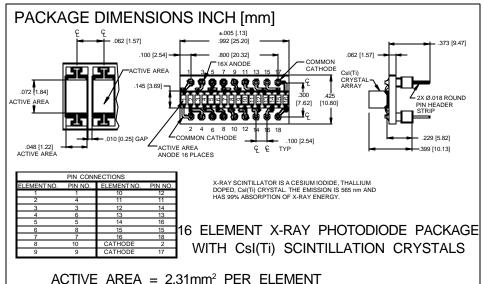
ELECTRO-OPTICAL CHARACTERISTICS (TA=25°C unless otherwise noted, without scintillator)

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	MIN	TYP	MAX	UNITS
ا عد	Short Circuit Current	H = 100 fc, 2850 K	18	28		μA
I _D	Dark Current	$H = 0, V_{R} = 5 V$		5	50	nA
R _{SH}	Shunt Resistance	$H = 0, V_{R} = 10 \text{ mV}$	100	200		MΩ
TCR _{SH}	RSH Temp. Coefficient	$H = 0, V_{R} = 10 \text{ mV}$		-8		% / °C
CJ	Junction Capacitance	$H = 0, V_{R} = 0 V^{**}$		40	60	pF
λrange	Spectral Application Range	Spot Scan	350		1100	nm
λρ	Spectral Response - Peak	Spot Scan		950		nm
V _{BR}	Breakdown Voltage	I = 10 µ. A	15	30		V
NEP	Noise Equivalent Power	V _R = 10 V @ Peak		2x10 ⁻¹⁴		W/ $\sqrt{_{Hz}}$
tr	Response Time	$RL = 50 \Omega V_R = 10 V$		15		nS

Information in this technical data sheet is believed to be correct and reliable. However, no responsibility is assumed for possible inaccuracies or omission. Specifications are subject to change without notice. ** f = 1 Mhz PAGE 3 OF 6 [FORMNO.100-PDB-707-100-XXREVE]

PHOTONIC 32 CHANNEL DETECTOR PRE-AMP BOARD ASSEMBLY **DETECTORS INC.** Type PDB-C216-C Used on PDB-707-100-DC





RESPONSIVITY (A/W)

FEATURES

- .062 inch centers
- Stackable
- Csl(Ti) crystals
- Low capacitance

DESCRIPTION

The **PDB-C216-C** is a common cathode, monolithic silicon PIN photodiode 16 element array. Designed to be stacked end to end to form a line of pixels. Supplied with X-Ray CsI(Ti) scintillation crystals.

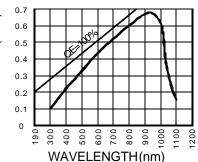
APPLICATIONS

- Luggage X-ray
- X-Ray scanner
- X-Ray inspection

ABSOLUTE MAXIMUM RATING (TA=25°C unless otherwise noted)

SYMBOL	PARAMETER	MIN	MAX	UNITS
OTWIDOL				
V _{BR}	Reverse Voltage		50	V
T _{STG}	Storage Temperature	-40	+100	°C
T _o	Operating Temperature Range	-20	+75	°C
Ts	Soldering Temperature*		+265	°C
Ι _L	Light Current		500	mA

SPECTRALRESPONSE



*1/16 inch from case for 3 secs max

ELECTRO-OPTICAL CHARACTERISTICS (TA=25°C unless otherwise noted, without scintillator)

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	MIN	TYP	MAX	UNITS
ع ع	Short Circuit Current	H = 100 fc, 2850 K	18	28		μA
I _D	Dark Current	$H = 0, V_{R} = 5 V$		5	50	nA
R _{sH}	Shunt Resistance	$H = 0, V_{R} = 10 \text{ mV}$	100	200		MΩ
TCR _{SH}	RSH Temp. Coefficient	$H = 0, V_{R} = 10 \text{ mV}$		-8		% / °C
CJ	Junction Capacitance	$H = 0, V_{R} = 0 V^{**}$		40	60	pF
λrange	Spectral Application Range	Spot Scan	350		1100	nm
λρ	Spectral Response - Peak	Spot Scan		950		nm
V _{BR}	Breakdown Voltage	I = 10 µ. A	15	30		V
NEP	Noise Equivalent Power	V _R = 10 V @ Peak		2x10 ⁻¹⁴		W/ √ Hz
tr	Response Time	$RL = 50 \Omega V_R = 10 V$		15		nS

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PHOTONIC32 CHANNEL DETECTOR PRE-AMP BOARD ASSEMBLY**DETECTORS INC.**Type PDB-707-100-XX

 $\label{eq:amplifier} \text{AMPLIFIER SPECIFICATION PER CHANNEL} \quad \text{TA} = 25^{\circ} \text{ C}, \text{V}^{\star} = 5 \text{ V}, \text{V}_{\text{cM}} = 1.5 \text{ V}, \text{V}_{\text{o}} = 2.5 \text{ V} \text{ and } \text{R}_{\text{L}} > 1 \text{ M} \quad \text{UNLESS OTHERWISE NOTED}$

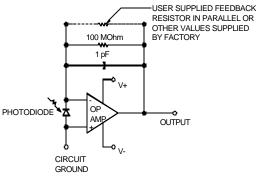
CHARACTERISTIC	TEST CONDITIONS	MIN	ТҮР	MAX	UNITS
INPUT OFFSET VOLTAGE (Vos)	INITIAL OFFSET		350	1000	μV
	LONGTERMOFFSETSTABILITY		15		μV/MONTH
AVERAGE INPUT OFFSET DRIFT (TCVos)	$R_{L} = 100 \text{ K}\Omega$		1		μV/°C
INPUT BIAS CURRENT (I₅)	OFFSETCURRENT, VCM=0			100	рА
INPUTOFFSETCURRENT(I∞)				100	рА
INPUT VOLTAGE RANGE (Ive)	COMMON MODE REJECTION VCM±10V	±11	±12		V
INPUT VOLTAGE NOISE (e,)	VOLTAGE 0, f=100 Hz		40		nV∕√Hz
	VOLTAGE 0, f=1 Khz		30		nV∕√Hz
INPUTCURRENTNOISE (in)	TYP f=1 KHz		1.8		fA/√Hz
FREQUENCYRESPONSE	UNITY GAIN, SMALL SIGNAL	0.8	1.0		MHz
	SLEW RATE, UNITY GAIN	1.0	1.8		V/ 113
CLOSED LOOP GAIN (CLBW)	AVCL=+5 V		9		Mhz
SUPPLYCURRENT(Isy)*	V = +15 V, V ₀ = 7.5 V		27.2	32	mA
SHORT CIRCUIT CURRENT			15		mA
POWER SUPPLY	OPERATING VOLTAGE	±4.5		±15.5	V

NOTE:8 EACH NATIONAL P/N: LMC6084, CMOS QUAD OPERATIONAL AMPLIFIER USED IN ASSEMBLY. * TOTAL ASSEMBLY SUPPLY CURRENT

AMPLIFIER ABSOLUTE MAXIMUM RATING (TA=25°C UNLESS OTHERWISE NOTED)

PARAMETER	MIN	MAX	UNITS				
SUPPLYVOLTAGE		16	±V				
DIFFERENTIAL INPUT VOLTAGE		±16	V				
STORAGETEMPERATURE	-55	+125	° C				
OPERATINGTEMPERATURE	0	+70	° C				

CAUTION: ESD SENSITIVE DEVICE

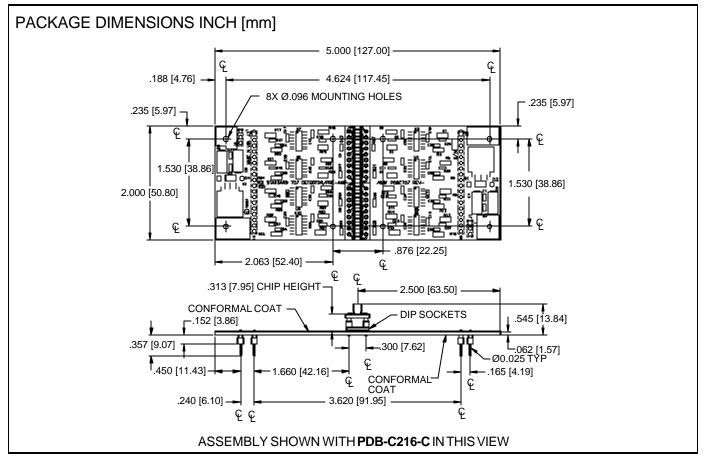


SINGLE OP-AMP STAGE SCHEMATIC

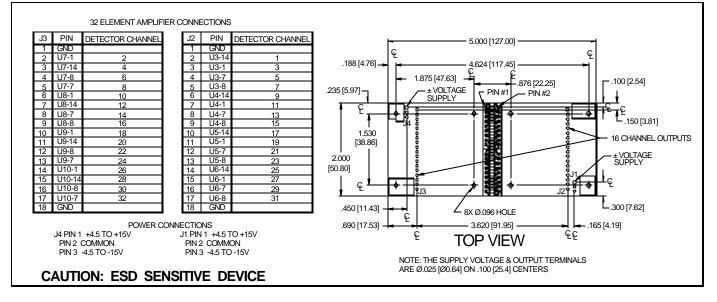
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PHOTONIC32 CHANNEL DETECTOR PRE-AMP BOARD ASSEMBLY**DETECTORS INC.**Type PDB-707-100-XX

MECHANICAL DIMENSIONS



ELECTRICALCONNECTIONS



Information in this technical data sheet is believed to be correct and reliable. However, no responsibility is assumed for possible inaccuracies or omission. Specifications are subject to change without notice. **PAGE 6 OF 6** [FORMNO.100-PDB-707-100-XXREVE]